

Abstract

The EL substrate includes semiconductor layers (22, 32) of TFTs (20, 30), a pixel electrode (51), and an upper part electrode (42) of a Cs section (40) which are provided on a gate insulating film (14). The semiconductor layers (22, 32) are covered with a protective film (17) which has openings (17a, 17b) via which the pixel electrode (51) and the upper part electrode (42) are exposed. The semiconductor layers (22, 32) are an oxide semiconductor layer (15), and the pixel electrode (51) and the upper part electrode (42) are reduction electrodes of the oxide semiconductor layer (15).
